









CSD13383F4

SLPS517B-DECEMBER 2014-REVISED DECEMBER 2017

CSD13383F4 12 V N-Channel FemtoFET™ MOSFET

Features 1

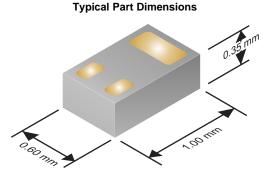
- Low On-Resistance
- Ultra Low Q_q and Q_{qd}
- Ultra-Small Footprint (0402 Case Size)
 - 1.0 mm × 0.6 mm
- Low Profile
 - 0.35 mm Height
- Integrated ESD Protection Diode
 - Rated >2 kV HBM
 - Rated >2 kV CDM
- Lead and Halogen Free
- **RoHS** Compliant

Applications 2

- Optimized for Load Switch Applications
- Optimized for General Purpose Switching Applications
- Single-Cell Battery Applications
- Handheld and Mobile Applications

Description 3

This 37 mΩ, 12 V N-channel FemtoFET™ MOSFET technology is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.



Product Summary

T _A = 25°	c	TYPICAL VA	UNIT	
V _{DS}	Drain-to-Source Voltage		V	
Qg	Gate Charge Total (4.5 V)	2.0	nC	
Q _{gd}	Gate Charge Gate-to-Drain	0.6		nC
Б	Drain-to-Source On-Resistance	$V_{GS} = 2.5 V$	53	mΩ
R _{DS(on)}	Drain-to-Source On-Resistance	$V_{GS} = 4.5 V$	37	mu
V _{GS(th)}	Threshold Voltage	1.0		V

Ordering Information⁽¹⁾

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD13383F4	3000	7-Inch	Femto (0402) 1.0 mm ×	Tape and
CSD13383F4T	250	Reel	0.6 mm SMD Lead Less	Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

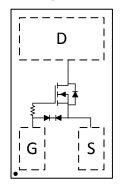
Absolute Maximum Ratings

T _A = 25	°C	VALUE	UNIT
V _{DS}	Drain-to-Source Voltage	12	V
V _{GS}	Gate-to-Source Voltage	±10	V
ID	Continuous Drain Current ⁽¹⁾	2.9	А
I _{DM}	Pulsed Drain Current ⁽¹⁾⁽²⁾	18.5	А
1	Continuous Gate Clamp Current	25	mA
I _G	Pulsed Gate Clamp Current ⁽¹⁾⁽²⁾	250	mA
PD	Power Dissipation	500	mW
ESD	Human Body Model (HBM)	2	kV
Rating	Charged Device Model (CDM)	2	kV
T _J , T _{stg}	Operating Junction Temperature Storage Temperature	–55 to 150	°C
E _{AS}	Avalanche Energy, single pulse I_D = 6.7, L = 0.1 mH, R_G = 25 Ω	2.2	mJ

(1) Typical $R_{\theta JA} = 250^{\circ}C/W$.

(2) Pulse duration ≤100 µs, duty cycle ≤1%.

Top View





TEXAS INSTRUMENTS

www.ti.com

Table of Contents

7.1

7.2

7.3

- 1Features12Applications13Description14Revision History25Specifications35.1Electrical Characteristics35.2Thermal Information3
 - 5.3 Typical MOSFET Characteristics 4
- 6 Device and Documentation Support......7

6.1Community Resources76.2Trademarks76.3Electrostatic Discharge Caution76.4Glossary77Mechanical, Packaging, and Orderable
Information8

Mechanical Dimensions 8

Device and Documentation Support.....

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	hanges from Revision A (January 2016) to Revision B	Page
•	Changed I _{DM} value From: 27 A To: 18.5 A in the <i>Absolute Maximum Ratings</i> table	1
•	Updated Figure 1.	4
•	Updated Figure 10 using Typ R _{θJA} = 250°C/W	5
•	Updated all mechanical drawings, increased the size of the pads in the Recommended Stencil Pattern section	8

CI	Changes from Original (December 2014) to Revision A						
•	Changed the t _{d(on)} value From: 39 ns To: 46 ns in the <i>Electrical Characteristics</i> table.	3					
•	Changed the t _r value From: 123 ns To: 122 ns in the <i>Electrical Characteristics</i> table.	3					
•	Changed the t _{d(off)} value From: 96 ns To: 250 ns in the <i>Electrical Characteristics</i> table.	3					
•	Changed the t _f value From: 315 ns To: 290 ns in the <i>Electrical Characteristics</i> table.	3					
•	Added Community Resources section.	7					

5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					
BV _{DSS}	Drain-to-source voltage	$V_{GS} = 0 V, I_{DS} = 250 \mu A$	12			V
I _{DSS}	Drain-to-source leakage current	$V_{GS} = 0 V, V_{DS} = 9.6 V$			1	μΑ
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 10 V			10	μA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}$, $I_{DS} = 250 \ \mu A$	0.70	1.00	1.25	V
D		$V_{GS} = 2.5 \text{ V}, \text{ I}_{DS} = 0.5 \text{ A}$		53	65	mΩ
R _{DS(on)}	Drain-to-source on-resistance	$V_{GS} = 4.5 \text{ V}, \text{ I}_{DS} = 0.5 \text{ A}$		37	44	mΩ
9 _{fs}	Transconductance	V _{DS} = 6 V, I _{DS} = 0.5 A		5.4		S
DYNAMI	C CHARACTERISTICS	· ·				
C _{iss}	Input capacitance			224	291	pF
C _{oss}	Output capacitance	$V_{GS} = 0 V, V_{DS} = 6 V,$ f = 1 MHz		68		pF
C _{rss}	Reverse transfer capacitance	J = 1 10112		47	61	pF
R _G	Series gate resistance			240		Ω
Qg	Gate charge total (4.5 V)			2.0	2.6	nC
Q _{gd}	Gate charge gate-to-drain			0.6		nC
Q _{gs}	Gate charge gate-to-source	$V_{DS} = 6 V, I_{DS} = 0.5 A$		0.4		nC
Q _{g(th)}	Gate charge at V _{th}			0.1		nC
Q _{oss}	Output charge	V _{DS} = 6 V, V _{GS} = 0 V		0.9		nC
t _{d(on)}	Turn on delay time			46		ns
t _r	Rise time	$V_{DS} = 6 V, V_{GS} = 4.5 V,$		122		ns
t _{d(off)}	Turn off delay time	$I_{DS} = 0.5 \text{ A}, R_G = 2 \Omega$		250		ns
t _f	Fall time			290		ns
DIODE C	CHARACTERISTICS	+			+	
V _{SD}	Diode forward voltage	I _{SD} = 0.5 A, V _{GS} = 0 V		0.7	1.0	V

5.2 Thermal Information

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{ hetaJA}$	Junction-to-ambient thermal resistance ⁽¹⁾		90		0C/M
	Junction-to-ambient thermal resistance ⁽²⁾		250		°C/W

(1) Device mounted on FR4 material with 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu.

(2) Device mounted on FR4 material with minimum Cu mounting area.

CSD13383F4

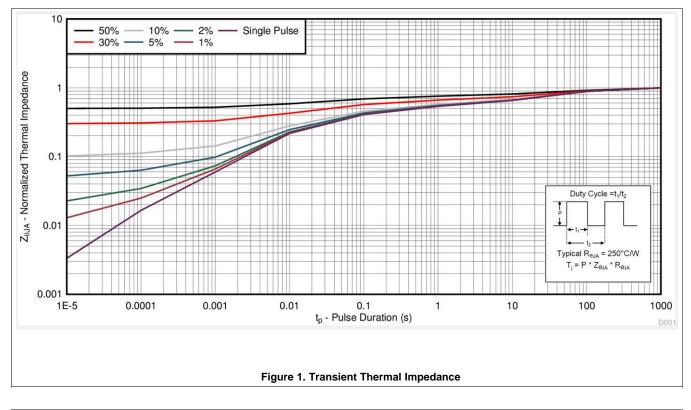
SLPS517B-DECEMBER 2014-REVISED DECEMBER 2017

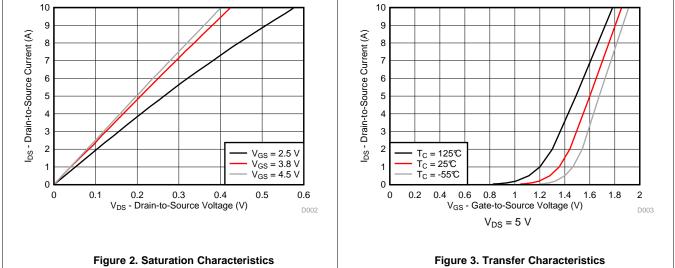
CSD13383F4

SLPS517B-DECEMBER 2014-REVISED DECEMBER 2017

5.3 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





4

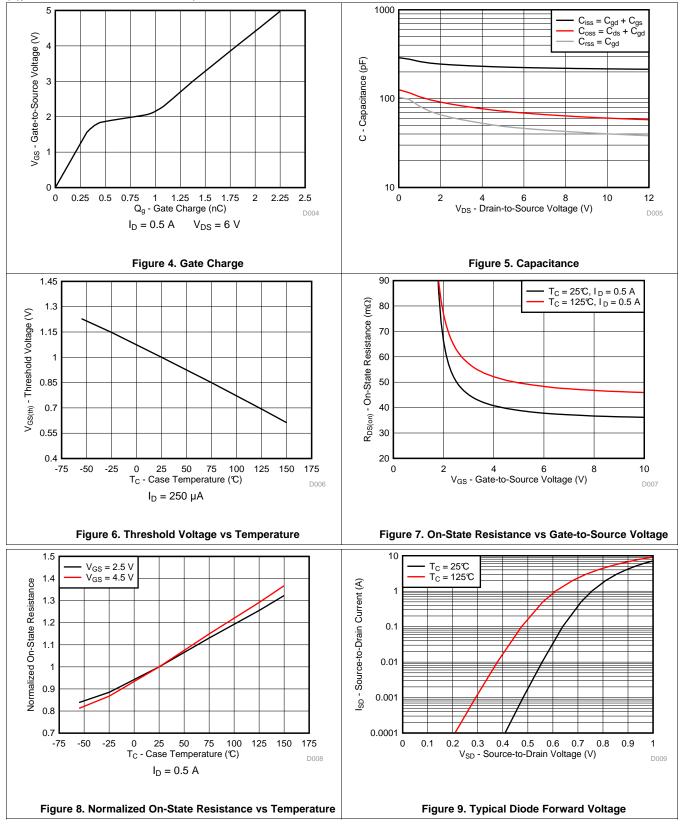


www.ti.com



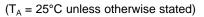
Typical MOSFET Characteristics (continued)

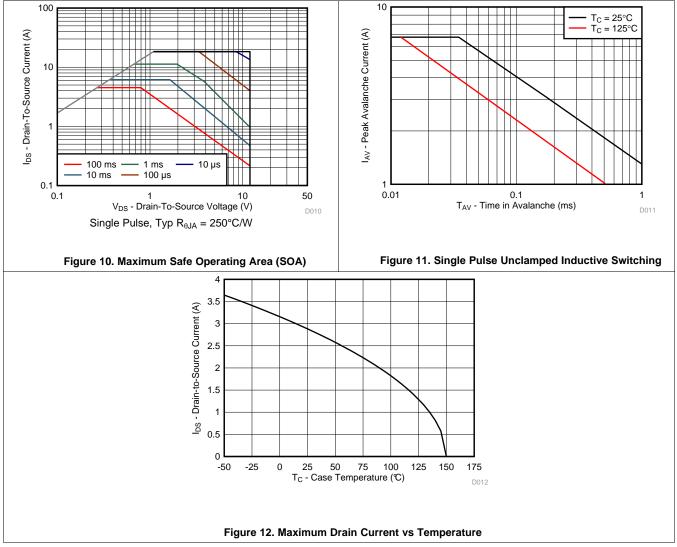
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





Typical MOSFET Characteristics (continued)







6 Device and Documentation Support

6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.2 Trademarks

FemtoFET, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

6.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.4 Glossary

SLYZ022 — TI Glossary.

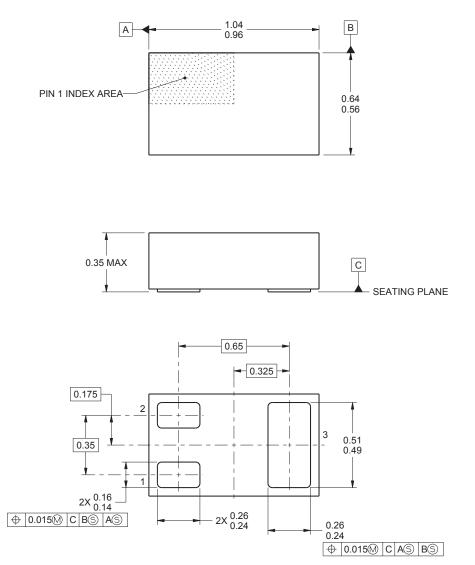
This glossary lists and explains terms, acronyms, and definitions.



7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

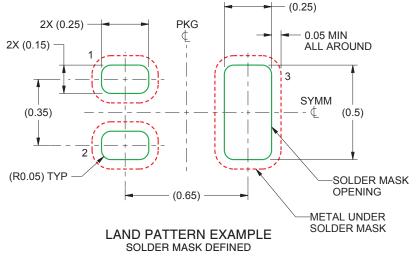
7.1 Mechanical Dimensions



- (1) All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- (2) This drawing is subject to change without notice.
- (3) This package is a Pb-free bump design. Bump finish may vary. To determine the exact finish, refer to the device data sheet or contact a local TI representative.

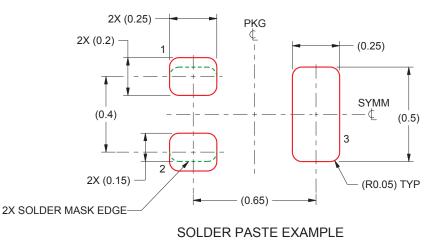


7.2 Recommended Minimum PCB Layout



- (1) All dimensions are in millimeters.
- (2) For more information, see QFN/SON PCB Attachment (SLUA271).

7.3 Recommended Stencil Pattern



- (1) All dimensions are in millimeters.
- (2) Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



12-Dec-2017

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD13383F4	ACTIVE	PICOSTAR	YJC	3	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM		GC	Samples
CSD13383F4T	ACTIVE	PICOSTAR	YJC	3	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM		GC	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



PACKAGE OPTION ADDENDUM

12-Dec-2017

PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD13383F4	PICOST AR	YJC	3	3000	178.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2
CSD13383F4	PICOST AR	YJC	3	3000	180.0	8.4	0.7	1.1	0.43	2.0	8.0	Q2
CSD13383F4T	PICOST AR	YJC	3	250	180.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

12-Dec-2017



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD13383F4	PICOSTAR	YJC	3	3000	220.0	220.0	35.0
CSD13383F4	PICOSTAR	YJC	3	3000	182.0	182.0	20.0
CSD13383F4T	PICOSTAR	YJC	3	250	182.0	182.0	20.0

IMPORTANT NOTICE

Texas Instruments Incorporated (TI) reserves the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete.

TI's published terms of sale for semiconductor products (http://www.ti.com/sc/docs/stdterms.htm) apply to the sale of packaged integrated circuit products that TI has qualified and released to market. Additional terms may apply to the use or sale of other types of TI products and services.

Reproduction of significant portions of TI information in TI data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such reproduced documentation. Information of third parties may be subject to additional restrictions. Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyers and others who are developing systems that incorporate TI products (collectively, "Designers") understand and agree that Designers remain responsible for using their independent analysis, evaluation and judgment in designing their applications and that Designers have full and exclusive responsibility to assure the safety of Designers' applications and compliance of their applications (and of all TI products used in or for Designers' applications) with all applicable regulations, laws and other applicable requirements. Designer represents that, with respect to their applications, Designer has all the necessary expertise to create and implement safeguards that (1) anticipate dangerous consequences of failures, (2) monitor failures and their consequences, and (3) lessen the likelihood of failures that might cause harm and take appropriate actions. Designer agrees that prior to using or distributing any applications that include TI products, Designer will thoroughly test such applications and the functionality of such TI products as used in such applications.

TI's provision of technical, application or other design advice, quality characterization, reliability data or other services or information, including, but not limited to, reference designs and materials relating to evaluation modules, (collectively, "TI Resources") are intended to assist designers who are developing applications that incorporate TI products; by downloading, accessing or using TI Resources in any way, Designer (individually or, if Designer is acting on behalf of a company, Designer's company) agrees to use any particular TI Resource solely for this purpose and subject to the terms of this Notice.

TI's provision of TI Resources does not expand or otherwise alter TI's applicable published warranties or warranty disclaimers for TI products, and no additional obligations or liabilities arise from TI providing such TI Resources. TI reserves the right to make corrections, enhancements, improvements and other changes to its TI Resources. TI has not conducted any testing other than that specifically described in the published documentation for a particular TI Resource.

Designer is authorized to use, copy and modify any individual TI Resource only in connection with the development of applications that include the TI product(s) identified in such TI Resource. NO OTHER LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE TO ANY OTHER TI INTELLECTUAL PROPERTY RIGHT, AND NO LICENSE TO ANY TECHNOLOGY OR INTELLECTUAL PROPERTY RIGHT OF TI OR ANY THIRD PARTY IS GRANTED HEREIN, including but not limited to any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information regarding or referencing third-party products or services does not constitute a license to use such products or services, or a warranty or endorsement thereof. Use of TI Resources may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

TI RESOURCES ARE PROVIDED "AS IS" AND WITH ALL FAULTS. TI DISCLAIMS ALL OTHER WARRANTIES OR REPRESENTATIONS, EXPRESS OR IMPLIED, REGARDING RESOURCES OR USE THEREOF, INCLUDING BUT NOT LIMITED TO ACCURACY OR COMPLETENESS, TITLE, ANY EPIDEMIC FAILURE WARRANTY AND ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF ANY THIRD PARTY INTELLECTUAL PROPERTY RIGHTS. TI SHALL NOT BE LIABLE FOR AND SHALL NOT DEFEND OR INDEMNIFY DESIGNER AGAINST ANY CLAIM, INCLUDING BUT NOT LIMITED TO ANY INFRINGEMENT CLAIM THAT RELATES TO OR IS BASED ON ANY COMBINATION OF PRODUCTS EVEN IF DESCRIBED IN TI RESOURCES OR OTHERWISE. IN NO EVENT SHALL TI BE LIABLE FOR ANY ACTUAL, DIRECT, SPECIAL, COLLATERAL, INDIRECT, PUNITIVE, INCIDENTAL, CONSEQUENTIAL OR EXEMPLARY DAMAGES IN CONNECTION WITH OR ARISING OUT OF TI RESOURCES OR USE THEREOF, AND REGARDLESS OF WHETHER TI HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES.

Unless TI has explicitly designated an individual product as meeting the requirements of a particular industry standard (e.g., ISO/TS 16949 and ISO 26262), TI is not responsible for any failure to meet such industry standard requirements.

Where TI specifically promotes products as facilitating functional safety or as compliant with industry functional safety standards, such products are intended to help enable customers to design and create their own applications that meet applicable functional safety standards and requirements. Using products in an application does not by itself establish any safety features in the application. Designers must ensure compliance with safety-related requirements and standards applicable to their applications. Designer may not use any TI products in life-critical medical equipment unless authorized officers of the parties have executed a special contract specifically governing such use. Life-critical medical equipment is medical equipment where failure of such equipment would cause serious bodily injury or death (e.g., life support, pacemakers, defibrillators, heart pumps, neurostimulators, and implantables). Such equipment includes, without limitation, all medical devices identified by the U.S. Food and Drug Administration as Class III devices and equivalent classifications outside the U.S.

TI may expressly designate certain products as completing a particular qualification (e.g., Q100, Military Grade, or Enhanced Product). Designers agree that it has the necessary expertise to select the product with the appropriate qualification designation for their applications and that proper product selection is at Designers' own risk. Designers are solely responsible for compliance with all legal and regulatory requirements in connection with such selection.

Designer will fully indemnify TI and its representatives against any damages, costs, losses, and/or liabilities arising out of Designer's noncompliance with the terms and provisions of this Notice.

> Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2017, Texas Instruments Incorporated